

FSS275 — N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		60	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		6	A
Drain Current (PW≤10s)	I _D	Duty cycle≤1%	6.5	A
Drain Current (PW≤10μs)	I _{DP}	Duty cycle≤1%	24	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (2000mm ² ×0.8mm), PW≤10s	1.9	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	60			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =3A	3.4	5.8		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =3A, V _{GS} =10V		33	43	mΩ
	R _{DS(on)2}	I _D =3A, V _{GS} =4V		44	62	mΩ

Marking : S275

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FSS275

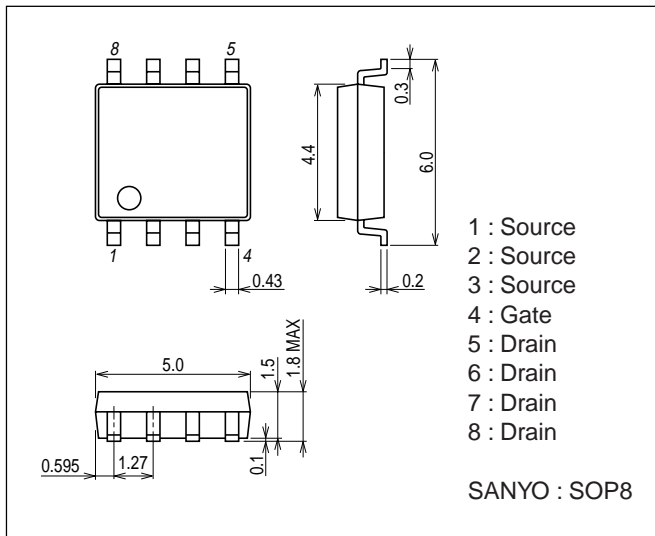
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz		1100		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		110		pF
Reverse Transfer Capacitance	Crss	V _{DS} =20V, f=1MHz		70		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		16		ns
Rise Time	t _r	See specified Test Circuit.		27		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		90		ns
Fall Time	t _f	See specified Test Circuit.		50		ns
Total Gate Charge	Q _g	V _{DS} =30V, V _{GS} =10V, I _D =6A		21		nC
Gate-to-Source Charge	Q _{gs}	V _{DS} =30V, V _{GS} =10V, I _D =6A		3.1		nC
Gate-to-Drain "Miller" Charge	Q _{gd}	V _{DS} =30V, V _{GS} =10V, I _D =6A		3.7		nC
Diode Forward Voltage	V _{SD}	I _S =6A, V _{GS} =0V		0.82	1.2	V

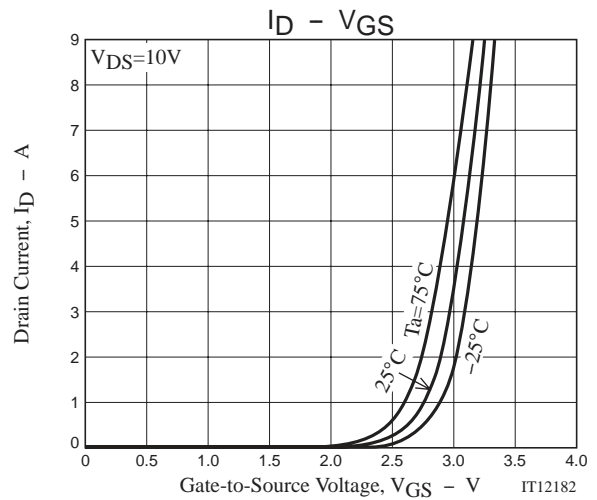
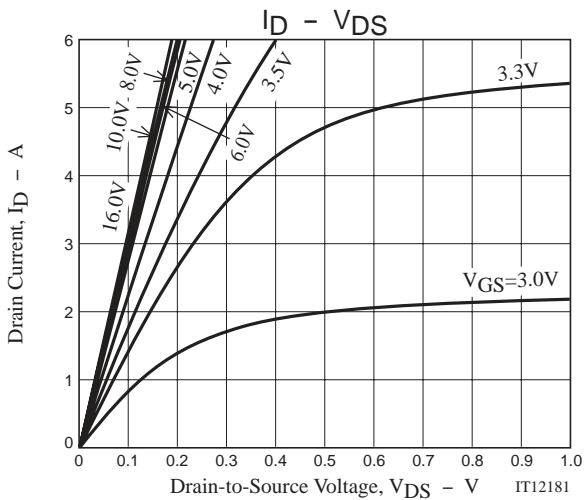
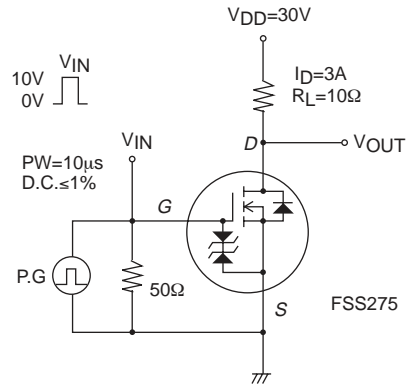
Package Dimensions

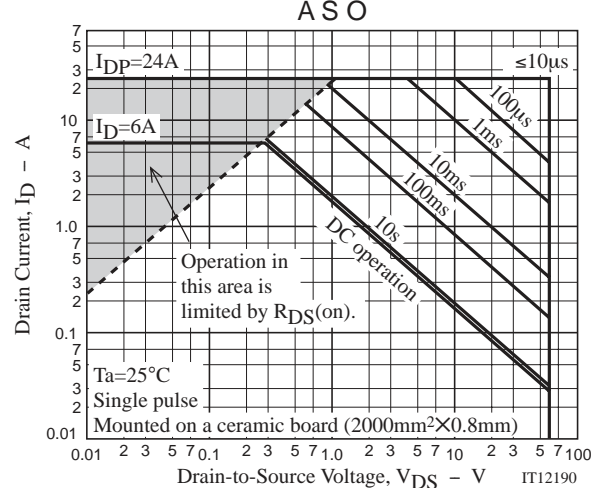
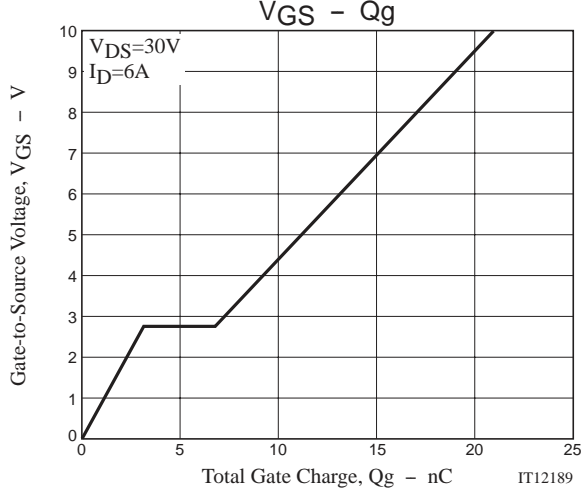
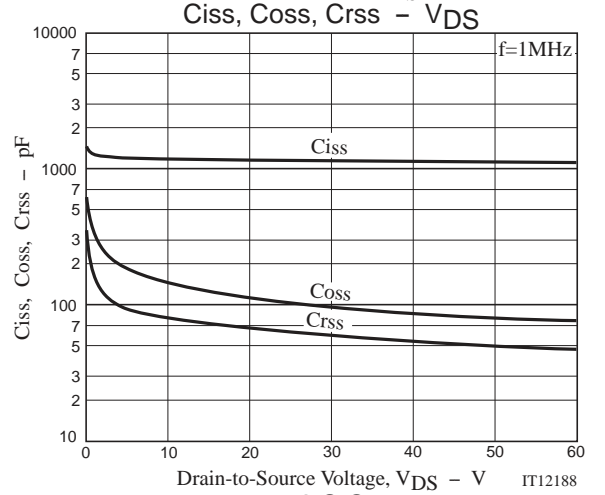
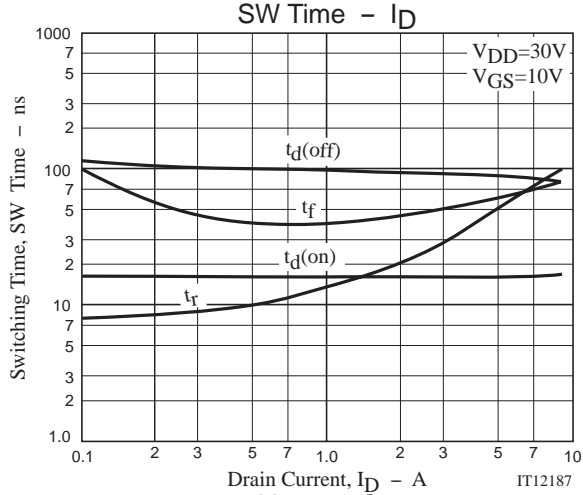
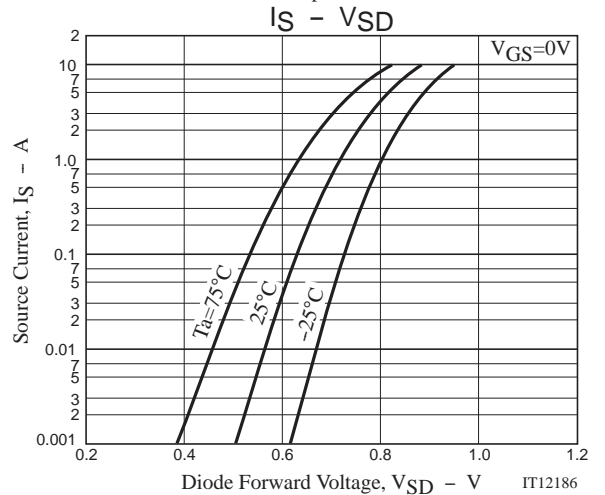
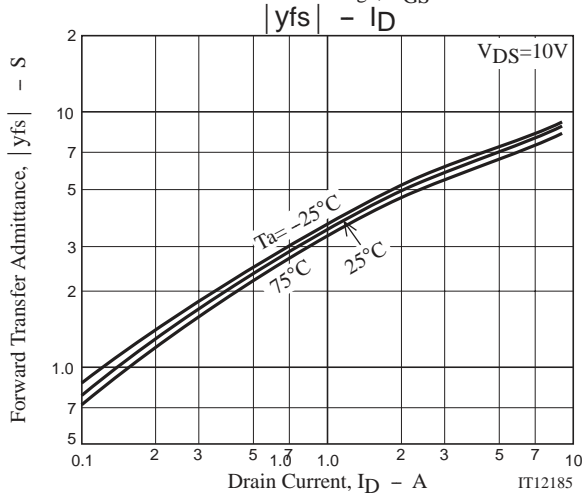
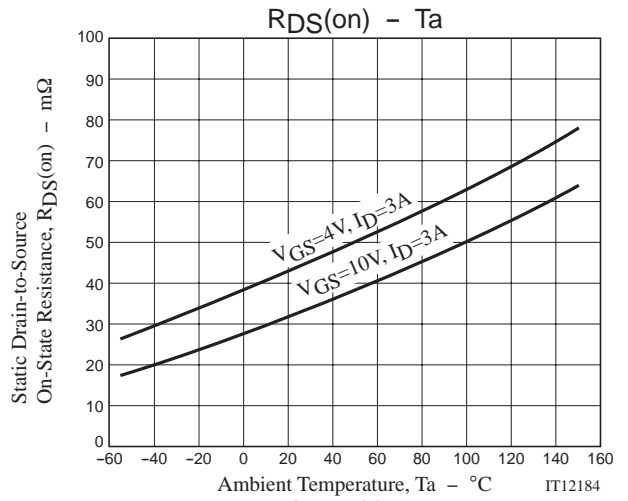
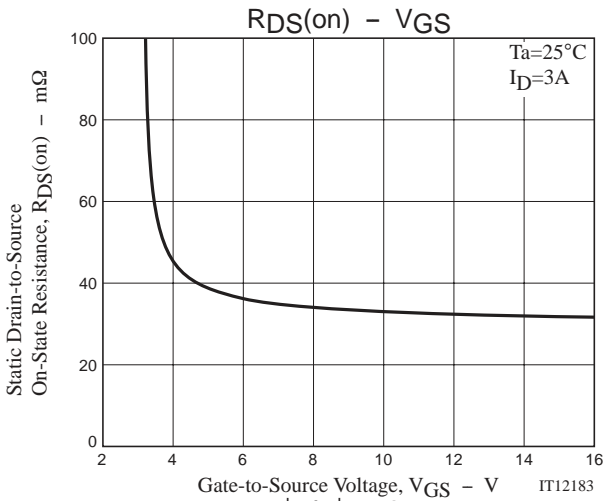
unit : mm (typ)

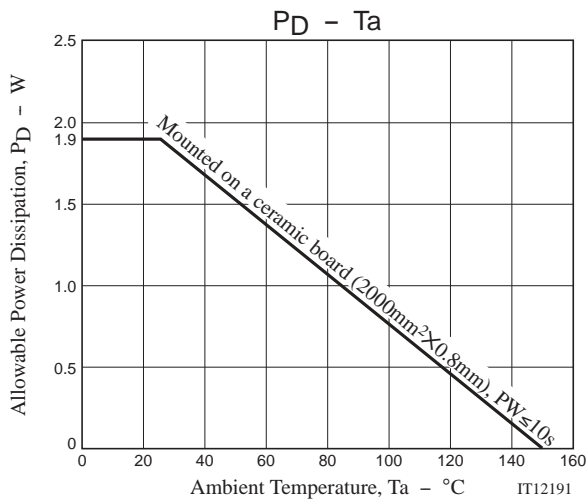
7005-002



Switching Time Test Circuit







Note on usage : Since the FSS275 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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